



Low Vcesat PNP Transistor

TO-126 Pin 1. 2. 3.

Pin Definition:

- 1. Emitter
- 2. Collector
- 3. Base

PRODUCT SUMMARY

BV _{CBO}	-50V
BV _{CEO}	-30V
I _C	-3A
V _{CE(SAT)}	$-0.5V @ I_C / I_B = -2A / -200mA$

<u>Features</u>

- Low $V_{CE(SAT)}$ -0.3 @ $I_C / I_B = 2A / 200mA$ (Typ.)
- Complementary part with TSD882

Structure

- Epitaxial Planar Type
- PNP Silicon Transistor

Ordering Information

Part No.	Package Packing		
TSB772CK B0G	TO-126	250pcs / Bulk	
TSB772CK C0G	TO-126	50pcs / Tube	

Note: "G" denote for Halogen Free Product

Absolute Maximum Rating (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Collector-Base Voltage		V _{CBO}	-50	V	
Collector-Emitter Voltage		V _{CEO}	-30	V	
Emitter-Base Voltage		V_{EBO}	-5	V	
Collector Current	DC		-3	А	
	Pulse	I _C	-7 (note)		
	$T_A = 25^{\circ}C$	1	1	W	
Collector Power Dissipation	$T_C = 25^{\circ}C$	P _D	10		
Operating Junction Temperature		T _J	+150	°C	
Operating Junction and Storage Temperature Range		T _{STG}	- 55 to +150	°C	

Note: Single pulse, Pw≤350us, Duty≤2%

Electrical Specifications (T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	$I_C = -50uA, I_E = 0$	BV _{CBO}	-50	-		V
Collector-Emitter Breakdown Voltage	$I_{\rm C} = -1 {\rm mA}, I_{\rm B} = 0$	BV _{CEO}	-30			V
Emitter-Base Breakdown Voltage	$I_E = -50uA, I_C = 0$	BV_{EBO}	-5			V
Collector Cutoff Current	$V_{CB} = -30V, I_{E} = 0$	I _{CBO}			-1	uA
Emitter Cutoff Current	$V_{EB} = 3V, I_{C} = 0$	I _{EBO}			-1	uA
Collector-Emitter Saturation Voltage	$I_C / I_B = -2A / -200mA$	*V _{CE(SAT)}		-0.3	-0.5	V
Base-Emitter Saturation Voltage	$I_C / I_B = -2A / -200mA$	*V _{BE(SAT)}		-1	-2	V
DC Current Transfer Ratio	$V_{CE} = -2V, I_{C} = -1A$	*h _{FE}	100		500	
Transition Frequency	V _{CE} =-5V, I _C =-100mA, f=100MHz	f _T		80		MHz
Output Capacitance	V _{CB} = -10V, f=1MHz	Cob		55		pF

^{*} Pulse Test: Pulse Width ≤380uS, Duty Cycle≤2%

1/4 Version: F13







Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

Figure 1. DC Current Gain

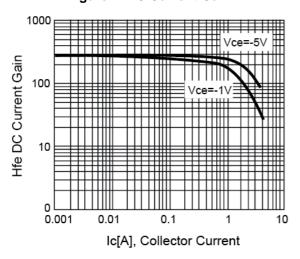


Figure 3. V_{BE(SAT)} v.s. Ic

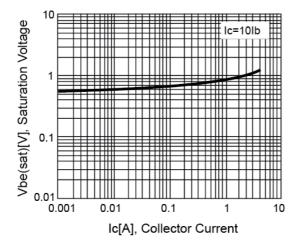


Figure 2. V_{CE(SAT)} v.s. Ic

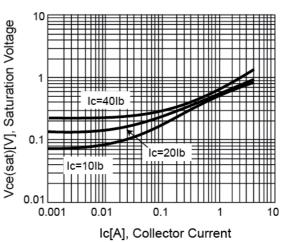
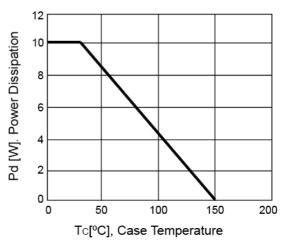


Figure 4. Power Derating Curve



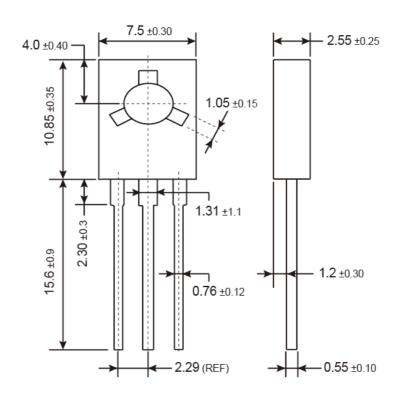
Version: F13

2/4



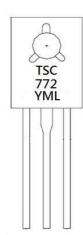


TO-126 Mechanical Drawing



Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product
 (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

3/4

L = Lot Code

Version: F13



TSB772 Low Vcesat PNP Transistor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

4/4 Version: F13